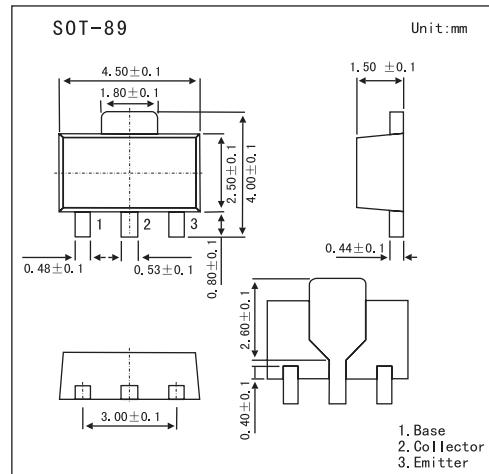


Small Signal Transistor

2SC3728

■ Features

- High h_{FE}=150 to 800.
- High collector current (I_c=2A).
- High collector dissipation P_c=500mW.
- Low V_{CE(sat)}: V_{CE(sat)}=0.17V typ(@I_c=1A,I_b=50mA).
- Small package for mounting.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	20	V
Emitter-base voltage	V _{EBO}	6	V
Collector-emitter voltage	V _{CEO}	12	V
Peak collector current	I _{CM}	3	A
Collector current	I _c	2	A
Collector dissipation (Ta=25°C)	P _c	500	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _c =10μA,I _e =0	20			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _e =10μA,I _c =0	6			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _c =5mA,R _{BE} =∞	12	14	16	V
Collector cutoff current	I _{cbo}	V _{CB} =16V,I _e =0			0.1	μA
Emitter cutoff current	I _{ebo}	V _{EB} =4V,I _c =0			0.1	μA
DC current gain	h _{FE}	V _{CE} =4V,I _c =100mA	150	350	800	
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =1A,I _b =50mA		0.2	0.35	V
Gain bandwidth product	f _t	V _{CE} =2V,I _e =-10mA	40	80		MHz
Collector output capacitance	C _{ob}	V _{CB} =10V,I _e =0,f=1MHz		28		pF

■ h_{FE} Classification

Marking	YE	YF	YG
h _{FE}	150~300	250~500	400~800